

<b>Form PTO-1449</b> <b>LIST OF PRIOR ART CITED BY APPLICANT</b>		ATTORNEY DOCKET NO.		SERIAL NO.	
		AUS9-2000-0733-US1		09/ 703,340	
		APPLICANT Berstis et al.			
		FILING DATE 10/31/00		GROUP ART UNIT 2841	
<b>U.S. PATENT DOCUMENTS</b>					
EXAMINER INITIAL	DOCUMENT NO.	PUBLICATION DATE	INVENTOR NAME	CLASS/ SUBCLASS	FILING DATE
<b>FOREIGN PATENT DOCUMENTS</b>					
EXAMINER INITIAL	DOCUMENT NO.	PUBLICATION DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES NO
<b>OTHER PRIOR ART (including author, title, date, pertinent page, etc.)</b>					
MLL		B. Prince, <u>Semiconductor Memories: A Handbook of Design, Manufacture, and Application, 2nd edition</u> , John Wiley & Sons, pp. 182-187, 07/1996.			
MLL		Weinberg, "On tunneling in metal-oxide-silicon structures", <u>J. Appl. Phys.</u> , v. 53, n. 7, pp. 5052-5056, 07/1982.			
MLL		Amin, "Design, selection, and implementation of flash erase EEPROM memory cells", <u>IEEE Proceedings-G</u> , v. 139, n. 3, pp. 370-376, 06/1992.			
MLL		Forbes, "Use of a spreadsheet for Fowler-Nordheim equation calculations", <u>J. Vac. Sci. Technol. B</u> , v. 17, n. 2, pp. 534-541, Mar/Apr. 1999.			
MLL		Lenzlinger et al., "Fowler-Nordheim Tunneling into Thermally Grown SiO <sub>2</sub> ", <u>J. Appl. Phys.</u> , v. 40, n. 1, pp. 278-283, 01/1969.			
MLL		Masuoka et al., "Reviews and Prospects of Non-Volatile Semiconductor Memories", <u>IEICE Transactions</u> , v. E 74, n. 4, 04/1991.			
MLL		Masuoka et al., "Flash Memories, Their Status and Trends", <u>Proceedings of 4th Intl. Conf. n Solid-State and Integrated Circuit Technology</u> , pp. 128-132, 10/1995.			
MLL		Chi et al., "True Low-Voltage Flash Memory Operations", <u>Proceedings of 1996 Intl. Nonvolatile Memory Technology Conference</u> , pp. 94-98, 04/1996.			
DATE CONSIDERED		EXAMINER			
2/19/02		Michael J. Lindgren			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

10/31/00